



USG08R044H

Preliminary

Power MOSFET

**N-CHANNEL SGT
ENHANCEMENT POWER
MOSFET**

■ DESCRIPTION

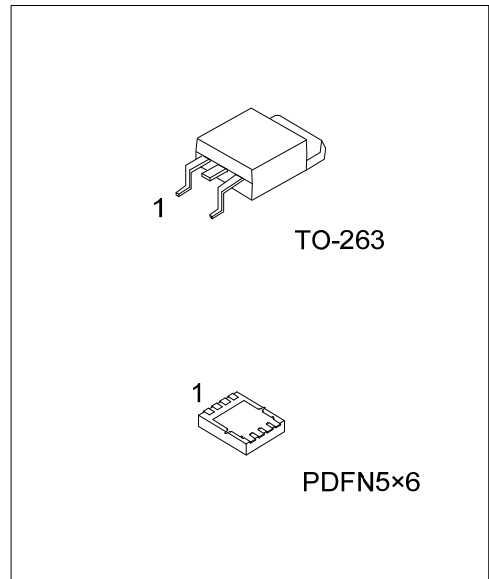
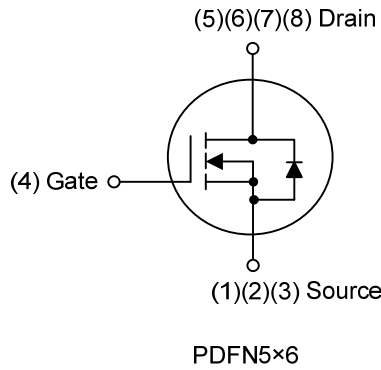
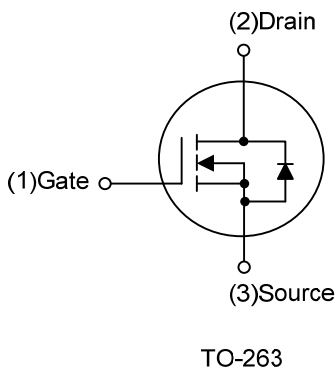
The UTC **USG08R044H** is a N-channel Power MOSFET, it uses UTC's advanced technology to provide the customers with high switching speed and low gate charge, etc.

The UTC **USG08R044H** applies to primary side switch, synchronous rectifier, Motor Drives, etc.

■ FEATURES

- * $R_{DS(ON)} \leq 4.4 \text{ m}\Omega @ V_{GS}=10V, I_D=50A$
- * High Cell Density Trench Technology
- * High Power and Current Handling Capability

■ SYMBOL



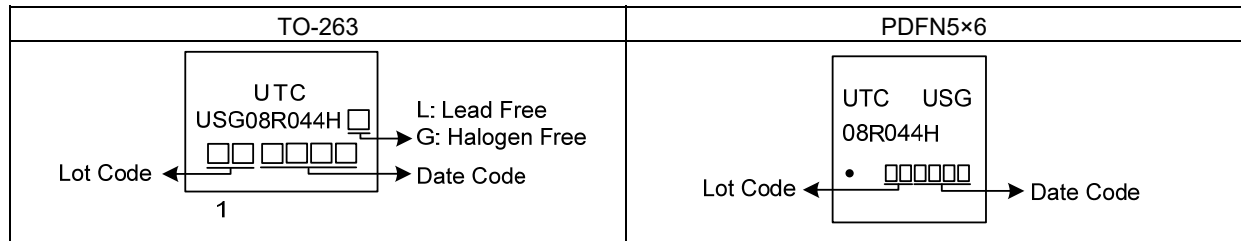
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
USG08R044HL-TQ2-T	USG08R044HG-TQ2-T	TO-263	G	D	S	-	-	-	-	-	Tube
USG08R044HL-TQ2-R	USG08R044HG-TQ2-R	TO-263	G	D	S	-	-	-	-	-	Tape Reel
USG08R044HL-P5060-R	USG08R044HG-P5060-R	PDFN5x6	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: S: Source G: Gate D: Drain

<p>USG08R044HG-TQ2-T</p>	<p>(1) T: Tube, R: Tape Reel (2) TQ2: TO-263, P5060: PDFN5x6 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	Continuous	I_D	140	A
	Pulsed (Note 2)	I_{DM}	280	A
Single Pulsed Avalanche Energy (Note 3)		E_{AS}	45	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.9	V/ns
Power Dissipation	TO-263	P_D	200	W
	PDFN5x6		45	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 0.1\text{mH}$, $I_{AS} = 30\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 30\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, $T_J \leq T_{JMAX}$, $T_J = 25^\circ\text{C}$.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-263	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	PDFN5x6		65	$^\circ\text{C}/\text{W}$
Junction to Case (Note)	TO-263	θ_{JC}	0.625	$^\circ\text{C}/\text{W}$
	PDFN5x6		2.77	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate Pc board, 2oz copper, with 1inch square copper plate.

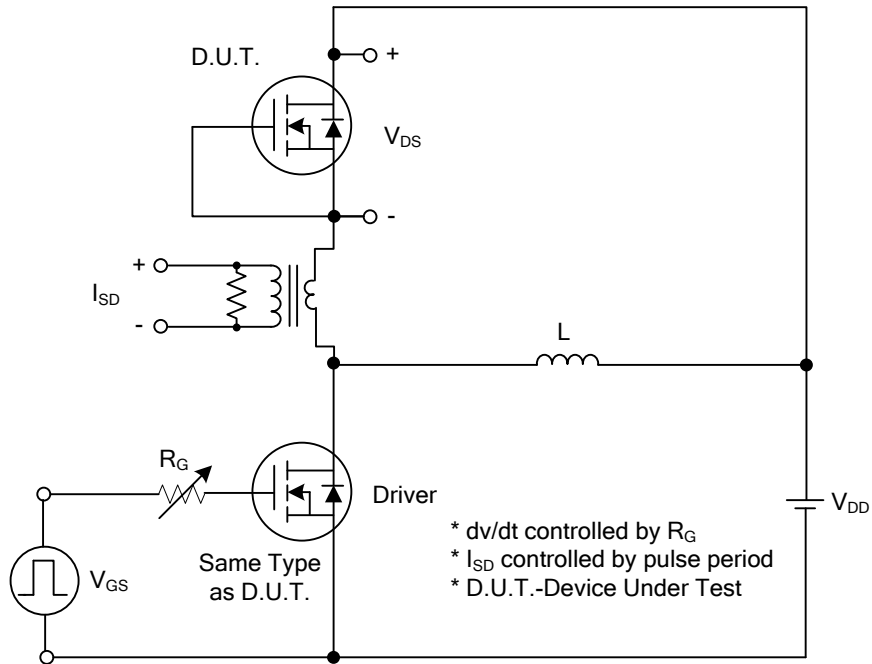
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	80			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=80\text{V}$, $V_{GS}=0\text{V}$			1	μA
Gate-Source Leakage Current	Forward	$V_{GS}=+20\text{V}$, $V_{DS}=0\text{V}$			+100	nA
	Reverse	$V_{GS}=-20\text{V}$, $V_{DS}=0\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=50\text{A}$			4.4	m Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$		4218		pF
Output Capacitance	C_{OSS}			1950		pF
Reverse Transfer Capacitance	C_{RSS}			348		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS}=64\text{V}$, $V_{GS}=10\text{V}$, $I_D=140\text{A}$		107		nC
Gate to Source Charge	Q_{GS}			20		nC
Gate to Drain Charge	Q_{GD}			45		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=40\text{V}$, $V_{GS}=10\text{V}$, $I_D=140\text{A}$, $R_G=3\Omega$		20		ns
Rise Time	t_R			25		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			50		ns
Fall-Time	t_F			30		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				140	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_F=30\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_S=30\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		62		ns
Body Diode Reverse Recovery Charge	Q_{rr}			114		nC

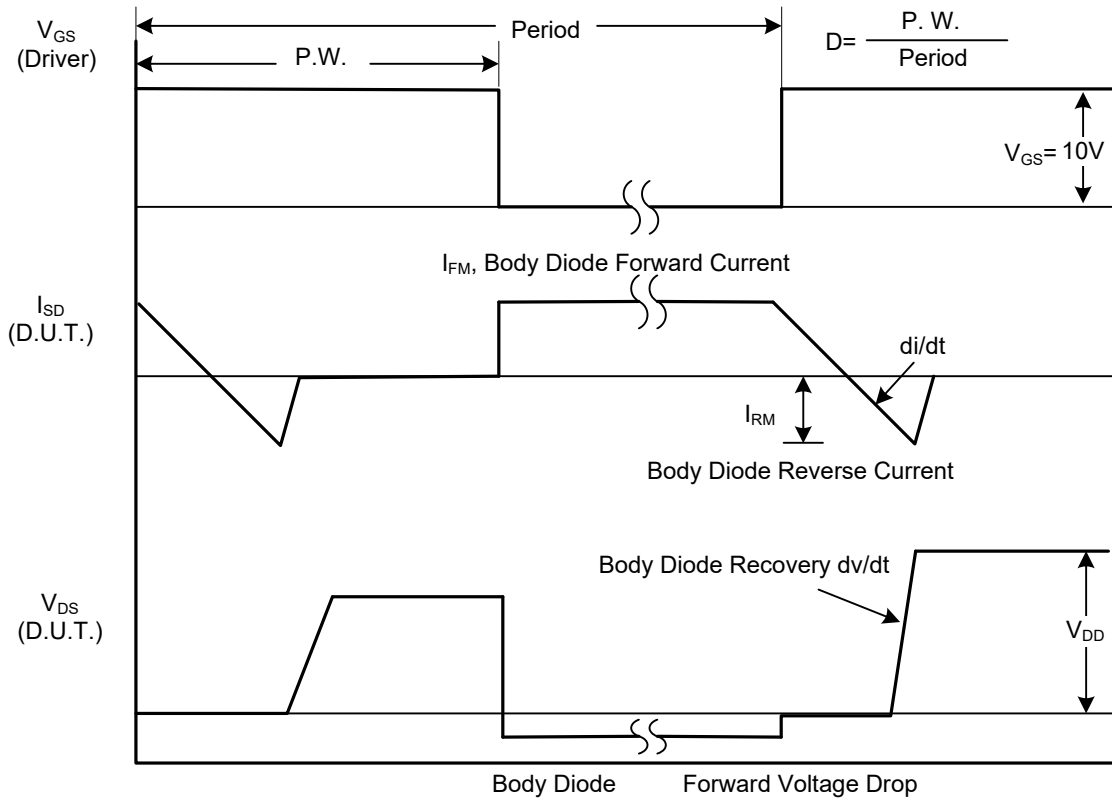
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

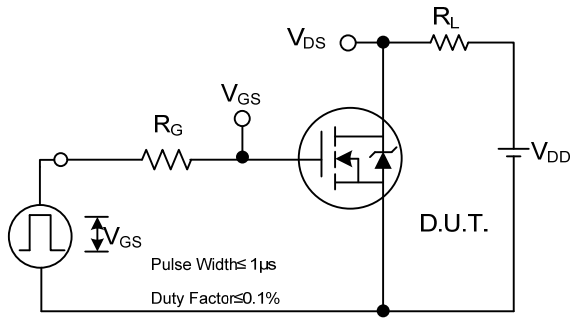


Peak Diode Recovery dv/dt Test Circuit

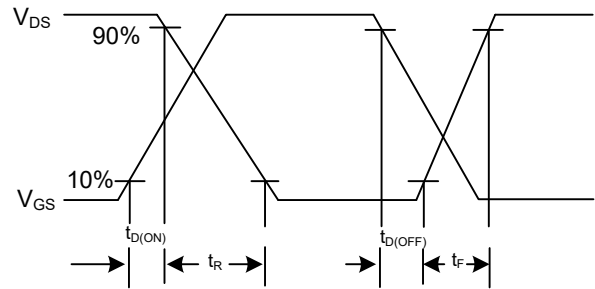


Peak Diode Recovery dv/dt Waveforms

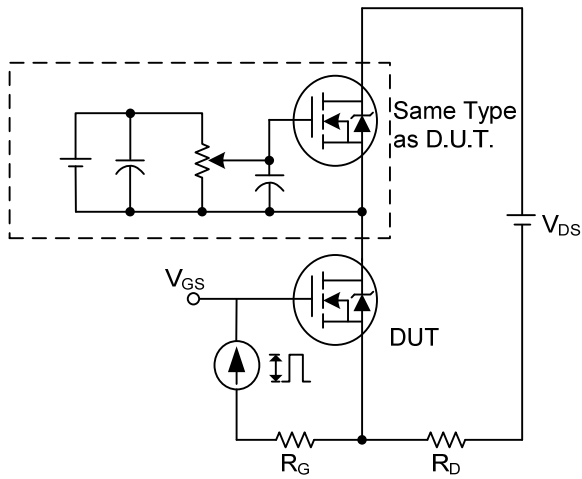
■ TEST CIRCUITS AND WAVEFORMS



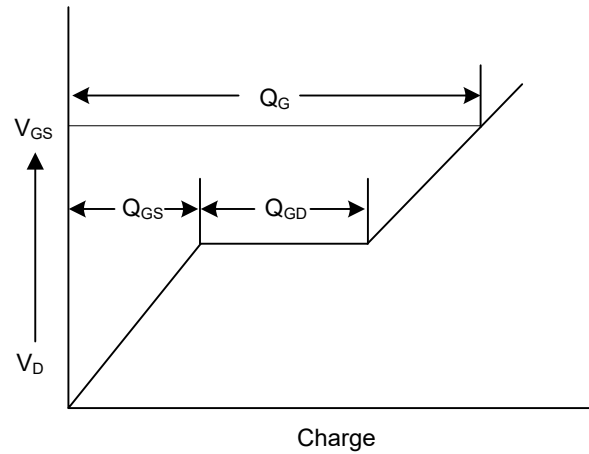
Switching Test Circuit



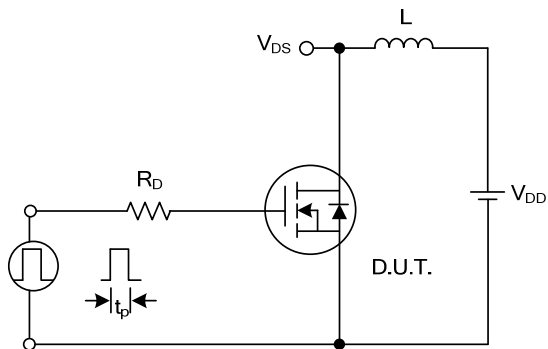
Switching Waveforms



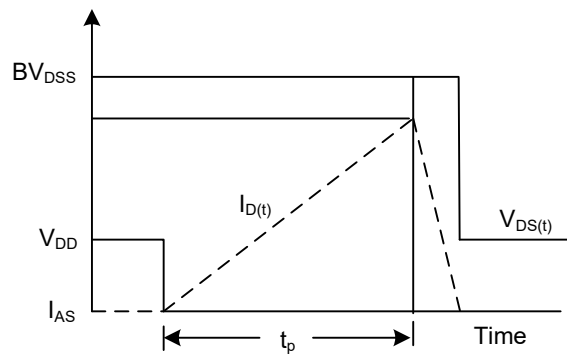
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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